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Docket No.: M4065.0210/P210-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Sam Yang et al.

Application No.: 10/002,176

Confirmation No.: 3795

Filed: December 5, 2001

Art Unit: 2814

For: METHOD OF FORMING A CAPACITOR FOR
A SEMICONDUCTOR DEVICE

Examiner: H. B. Trinh

INTERVIEW SUMMARY

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicants appreciate Examiner Trinh's and Examiner Weiss' time and attention during an interview held with Applicants' representative on February 21, 2007. During the interview, the reference Iizuka and claim 1 of the present application were discussed, but no agreement could be reached.

Dated: February 22, 2007

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371
DICKSTEIN SHAPIRO LLP
1825 Eye Street, NW
Washington, DC 20006-5403
(202) 420-2200
Attorney for Applicant